



浙江世菱半导体有限公司  
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

## 产品规格书

### Specification of products

产品名称：可控硅模块

产品型号：MFC500A-Y10

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ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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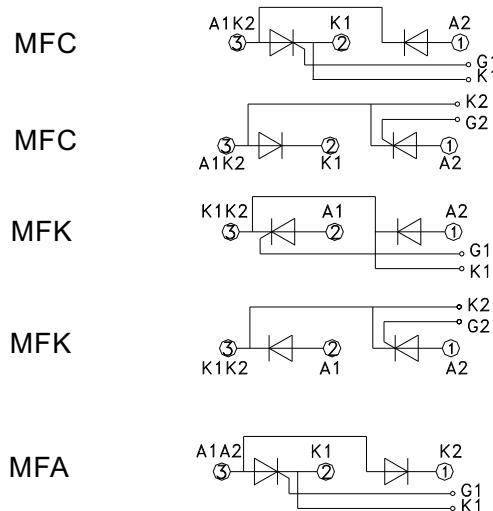
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拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J$ (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$ $I_{F(AV)}$	Mean on-state current	180° half sinewave 50Hz Single side cooled, $T_c=85^\circ C$	125			500	A
$I_{T(RMS)}$	RMS on-state current	Single side cooled, $T_c=85^\circ C$	125			785	A
$V_{DRM}$ $V_{RRM}$	Repetitive peakoff-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}$ tp=10ms $V_{DsM} \& V_{RsM} = V_{DRM} \& V_{RRM} + 200V$ respectively	125	600		1800	V
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	at $V_{DRM}$ at $V_{RRM}$	125			40	mA
$I_{TSM}$	Surge on-state current	10ms half sine wave	125			16.0	KA
$I^2t$	$I^2T$ for fusing coordination	$V_R=60\%V_{RRM}$				1310 $A^2s*10^3$	
$V_{TO}$	Threshold voltage		125			0.80	V
$r_T$	On-state slop resistance					0.34	$m\Omega$
$V_{TM}$	Peak on-state voltage	$I_{TM}=1500A$	125			1.5	V
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			800	V/ $\mu s$
$di/dt$	Critical rate of rise of on-state current	From 67% $V_{DRM}$ to 1500A, Gate source 1.5A $t_r \leq 0.5 \mu s$ Repetitive	125			150	A/ $\mu s$
$I_{GT}$	Gate trigger current		25	30		200	mA
$V_{GT}$	Gate trigger voltage	$V_A=12V, I_A=1A$		0.8		3.0	V
$I_H$	Holding current			20		100	mA
$V_{GD}$	Non-trigger gate voltage	At 67% $V_{DRM}$	125			0.2	V
$R_{th(j-c)}$	Thermal resistance Junction to heatsink	At 180° sine Single side cooled				0.065	$^\circ C /W$
$V_{iso}$	Isolation voltage	50Hz, RM. S, t=1min, $I_{iso}: 1mA$ (MAX)	2500				V
$F_m$	Thermal connection torque (M10)				9.0		N.m
	Mounting torque (M6)				5.0		N.m
$T_{stg}$	Stored temperature			-40		140	$^\circ C$
$W_t$	Weight				1575		g
Outline							

## OUTLINE DRAWING & CIRCUIT DIAGRAM



## Rating and Characteristic

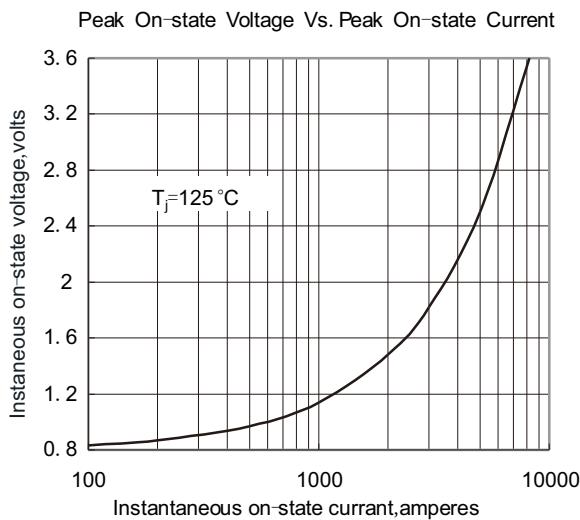


Fig. 1

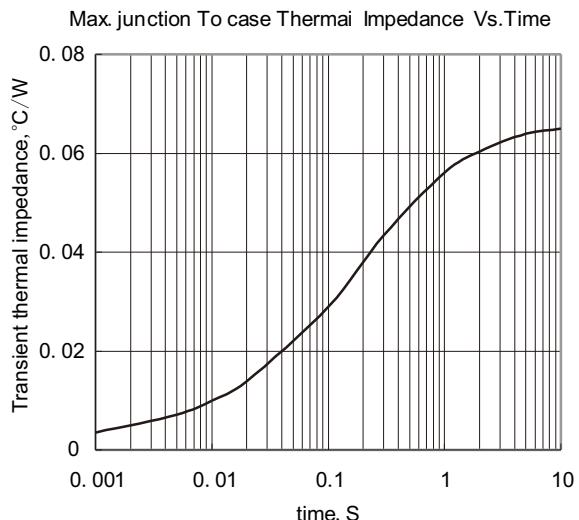


Fig. 2

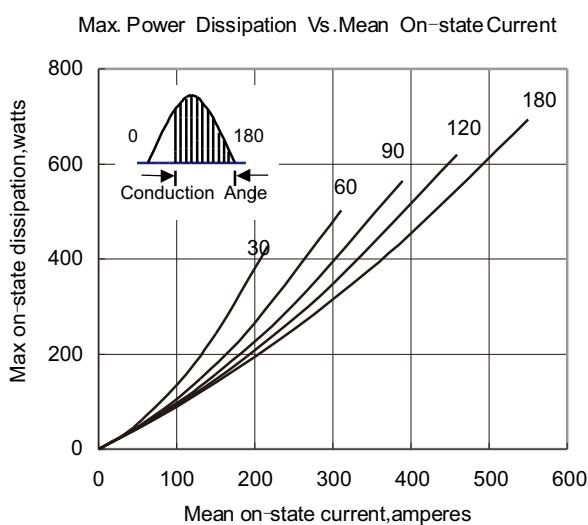


Fig. 3

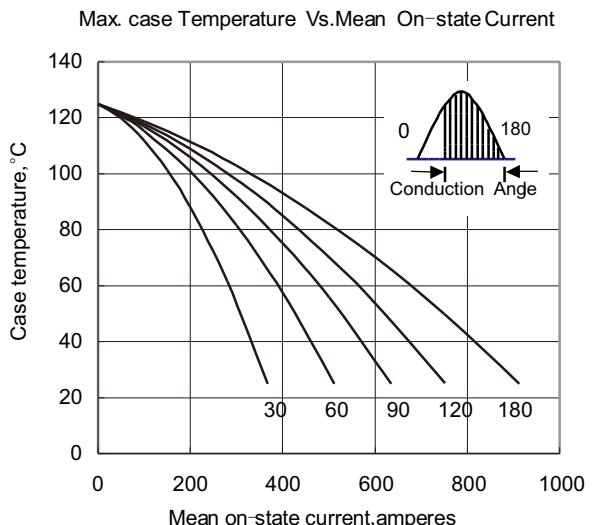


Fig. 4

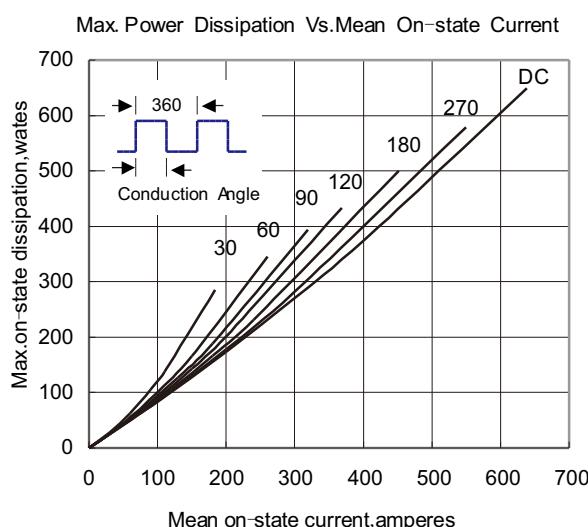


Fig. 5

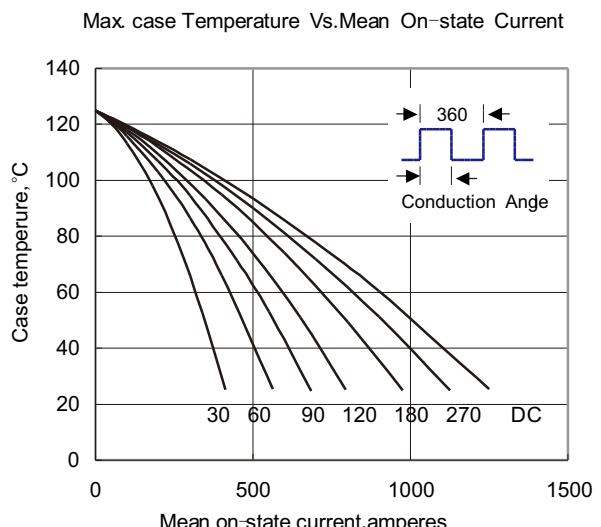


Fig. 6

## Rating and Characteristic

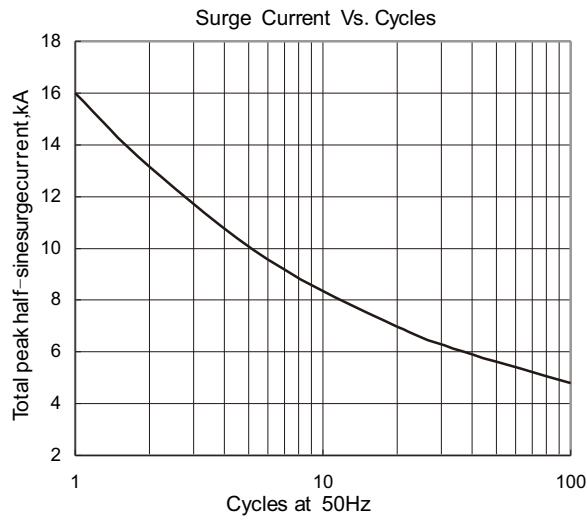


Fig. 7

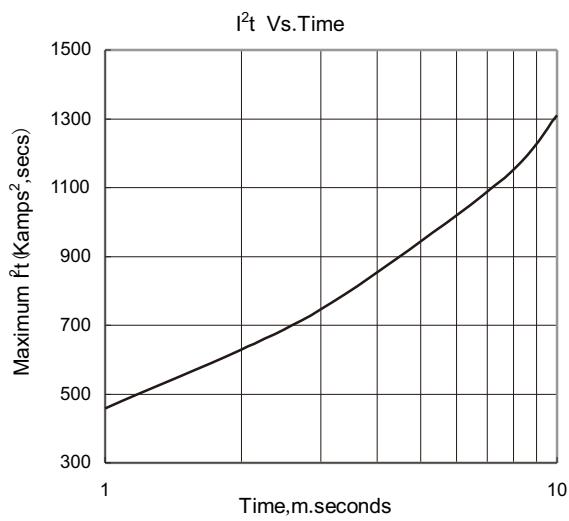


Fig. 8

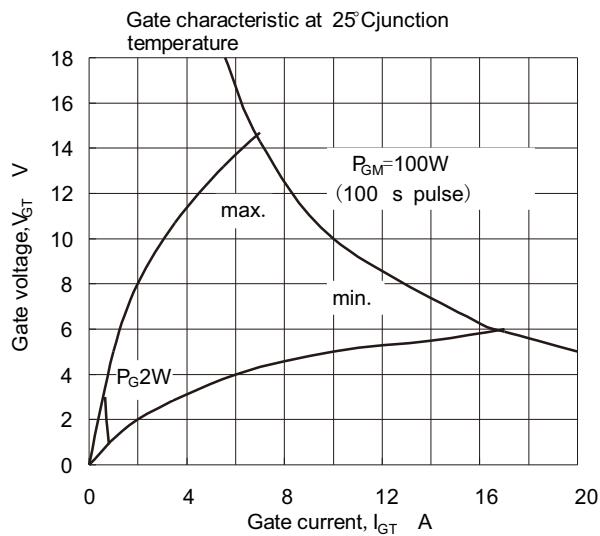


Fig. 9

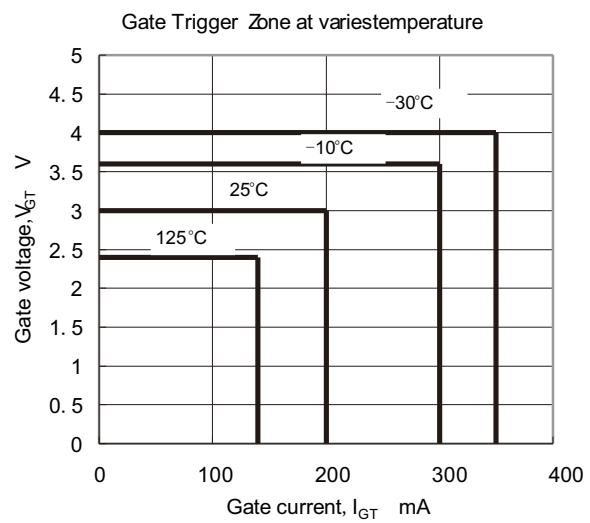


Fig. 10

## Outside Dimension

